



# Synthesis, spectroscopy, and efficient laser operation of “mixed” sesquioxide Tm:(Lu,Sc)<sub>2</sub>O<sub>3</sub> transparent ceramics

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**Abstract:** A novel transparent 4.76 at.% Tm:(Lu<sub>2/3</sub>Sc<sub>1/3</sub>)<sub>2</sub>O<sub>3</sub> “mixed” sesquioxide ceramic is synthesized by hot isostatic pressing (HIP) at 1800 °C / 195 MPa in an Ar atmosphere. Its structure is studied by scanning electron microscopy, X-ray diffraction, and Raman spectroscopy. The spectroscopic properties of the Tm<sup>3+</sup> ion are described within the Judd-Ofelt theory, which resulted in intensity parameters of  $\Omega_2 = 2.429$ ,  $\Omega_4 = 1.078$  and  $\Omega_6 = 0.653$  [ $10^{-20}$  cm<sup>2</sup>]. For the <sup>3</sup>F<sub>4</sub> → <sup>3</sup>H<sub>6</sub> transition, the maximum stimulated-emission cross-section  $\sigma_{SE}$  is  $7.15 \times 10^{-21}$  cm<sup>2</sup> at 1951 nm. The radiative lifetime of the <sup>3</sup>F<sub>4</sub> state is 4.01 ms. Under diode-pumping at 802 nm, a microchip Tm:(Lu,Sc)<sub>2</sub>O<sub>3</sub> ceramic laser generated ~1 W at 2100 nm with a slope efficiency of 24%. The spectroscopic and laser properties of the Tm:(Lu,Sc)<sub>2</sub>O<sub>3</sub> ceramic are compared with those of a Tm:LuScO<sub>3</sub> single crystal. The ceramic exhibits very broad and flat gain cross sections, which is promising for ultrashort pulse generation.

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## 1. Introduction

Cubic (C-type, bixbyite structure) rare-earth sesquioxides  $\text{A}_2\text{O}_3$  (where A = Lu, Y, Sc, etc.) are well known host crystals for trivalent laser-active lanthanide ions ( $\text{Ln}^{3+}$ ) such as  $\text{Yb}^{3+}$ ,  $\text{Tm}^{3+}$  or  $\text{Ho}^{3+}$  [1]. They feature good thermal and thermo-optical properties (high thermal conductivity,  $\kappa = 12.8$  W/mK for  $\text{Lu}_2\text{O}_3$  which is weakly dependent on the  $\text{Ln}^{3+}$  concentration

[2], and positive  $dn/dT$  coefficients [3]), broad transparency range (0.22–8  $\mu\text{m}$ ) and high refractive index ( $\sim 1.91$  for  $\text{Lu}_2\text{O}_3$  at  $\sim 1 \mu\text{m}$ ) [1], one of the lowest maximum phonon frequencies among the oxide matrices [1], as well as broad spectral bands for the  $\text{Ln}^{3+}$  dopant ions [1,4,5]. Efficient, wavelength-tunable and power-scalable near-IR Ln-doped sesquioxide lasers operating in the continuous-wave (CW) [1,6,7] and mode-locked (ML) regimes (at  $\sim 1$  and  $\sim 2 \mu\text{m}$ ) [8–10] have already been reported. These crystals have also been recognized to be very suitable for thin-disk oscillators [11,12].

Cubic  $\text{A}_2\text{O}_3$  crystals are in particular attractive for thulium lasers. The  $\text{Tm}^{3+}$  ion (electronic configuration:  $[\text{Xe}]4f^{12}$ ) is known for its emission around 2  $\mu\text{m}$  due to the  ${}^3\text{F}_4 \rightarrow {}^3\text{H}_6$  4f-4f electronic transition [13]. This eye-safe emission is used in range-finding, environmental sensing (LIDAR) and medicine. The  $\text{Tm}^{3+}$  ions can be excited by commercial AlGaAs laser diodes at  $\sim 0.8 \mu\text{m}$  (into the  ${}^3\text{H}_4$  state) while the possible cross-relaxation process,  ${}^3\text{H}_4 + {}^3\text{H}_6 \rightarrow {}^3\text{F}_4 + {}^3\text{F}_4$ , increases the excitation quantum efficiency [14]. In cubic  $\text{A}_2\text{O}_3$  crystals they feature a strong Stark splitting of the ground state ( ${}^3\text{H}_6$ ),  $> 800 \text{ cm}^{-1}$ , leading to very broad emission and gain spectra extending up to  $\sim 2.1 \mu\text{m}$  [1,5,6] which is much longer than for many other  $\text{Tm}^{3+}$ -doped oxide crystals. Moreover, this feature can be enhanced in “mixed”  $\text{Tm}:(\text{Lu}_{1-x},\text{Sc}_x)_2\text{O}_3$  crystals exhibiting a compositional disorder. A 1 at.%  $\text{Tm}:\text{LuScO}_3$  sesquioxide crystal was previously studied in [15] generating a CW output power of 705 mW at  $\sim 2.1 \mu\text{m}$  with a slope efficiency of 55% (under Ti:Sapphire laser pumping). A 155 nm-broad (1960–2115 nm) tuning range of the laser emission was demonstrated [15]. In the ML regime, 105 fs pulses were achieved at 2010 nm using a semiconductor saturable absorber mirror (SESAM) [16]. This corresponded to the shortest pulse duration ever reported for any ML  $\text{Tm}^{3+}:\text{A}_2\text{O}_3$  oscillator, proving the potential of “mixed” crystals for fs ML lasers.

Due to the high melting point of the cubic  $\text{A}_2\text{O}_3$  crystals (2450  $^\circ\text{C}$  for  $\text{Lu}_2\text{O}_3$ ), their growth typically requires the use of expensive rhenium (Rh) crucibles [17]. Rh can be the source of crystal coloration. The growth of large-volume highly  $\text{Tm}^{3+}$ -doped single crystals with high optical quality is complicated. The technology of  $\text{Tm}^{3+}$ -doped sesquioxide transparent ceramics was proposed as an alternative allowing for an easier and size-scalable production. There are multiple reports on  $\text{Tm}:\text{Lu}_2\text{O}_3$  transparent ceramics [18,19]. In [18], a 2 at.%  $\text{Tm}:\text{Lu}_2\text{O}_3$  ceramic laser generated 26 W at 2066 nm with a slope efficiency of 42%. Bulk fs ML lasers [20] and thin-disk lasers [21] based on  $\text{Tm}:\text{Lu}_2\text{O}_3$  ceramic are also known.

In the present work, we focused on a novel “mixed”  $\text{Tm}:(\text{Lu}_{2/3}\text{Sc}_{1/3})_2\text{O}_3$  transparent ceramic exhibiting promising potential for ultrafast lasers and amplifiers. We present structural and detailed spectroscopic characterization and compare this ceramic with a  $\text{Tm}:\text{LuScO}_3$  single-crystal. In addition to the ease of fabrication, we demonstrate that this new ceramic material can provide superior laser characteristics in comparison with the previously studied “mixed”  $\text{Tm}:\text{LuScO}_3$  ceramics [22] and single-crystals [15].

## 2. Fabrication of the $\text{Tm}:(\text{Lu,Sc})_2\text{O}_3$ ceramics

The  $\text{Tm}:(\text{Lu,Sc})_2\text{O}_3$  ceramics were fabricated by the Hot Isostatic Pressing (HIP) sintering method using powders of  $\text{Sc}_2\text{O}_3$ ,  $\text{Lu}_2\text{O}_3$ , and  $\text{Tm}_2\text{O}_3$  (purity: 99.99%, Alfa Aesar) as raw materials. The raw materials, with a stoichiometric amount of 100 at.% Lu + Sc (taken in a proportion of Lu:Sc = 2:1) and 5 at.% Tm over it, were mixed uniformly by ball milling for 24 h, dried for 6 h at 70  $^\circ\text{C}$ , sieved, dry-pressed at 10 MPa, and cold isostatically pressed at 200 MPa. The green bodies of  $\text{Tm}:(\text{Lu,Sc})_2\text{O}_3$  ceramics were firstly pre-sintered at 1750  $^\circ\text{C}$  for 10 h under vacuum (pressure,  $P < 10^{-3}$  Pa) to densify the preforms. For further densification, the pre-sintered  $\text{Tm}:(\text{Lu,Sc})_2\text{O}_3$  ceramic samples were post-sintered by HIP at 1800  $^\circ\text{C}$  for 2 h in an Ar atmosphere ( $P = 195$  MPa) to eliminate the closed pores around the grain boundaries. Finally, the ceramics were annealed at 1500  $^\circ\text{C}$  for 10 h in an  $\text{O}_2$  atmosphere to eliminate the oxygen vacancies and remove internal stresses. Samples of  $\text{Tm}:(\text{Lu,Sc})_2\text{O}_3$  ceramics with a diameter of 15 mm and a thickness of 5 mm were obtained. Some polished samples are shown in Fig. 1(a). For the spectroscopic experiments,  $3 \times 3 \times 3$



$\mu\text{m}$ , as determined by the linear intercept method. The grain size distribution is uniform over the sample cross-section.

### 3. Optical spectroscopy

#### 3.1 Optical absorption

The absorption spectrum of the  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  ceramic was measured using a Varian CARY 5000 spectrophotometer (Agilent) with a resolution of 0.2 nm. In addition to RT studies, we measured the absorption spectra at 6 K using an Oxford Instruments Ltd. cryostat (Model SU 12) with He-gas close-cycle flow. From the absorption coefficient  $\alpha_{\text{abs}}$  measured at RT, we calculated the RT absorption cross-section,  $\sigma_{\text{abs}} = \alpha_{\text{abs}}/N_{\text{Tm}}$ , where  $N_{\text{Tm}} = 13.8 \times 10^{20} \text{ cm}^{-3}$  corresponds to 4.76 at.% Tm doping.

The transmission of the laser-grade polished 3 mm-thick  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  ceramic sample measured at 2.15  $\mu\text{m}$  (out of the absorption band of  $\text{Tm}^{3+}$ ) was  $\sim 77\%$  which is slightly lower than the value arising purely from the Fresnel losses expected for this material (81.1%, if assuming a refractive index  $n$  of 1.92). No noticeable distortion or scattering of the probe He-Ne laser beam passing through the sample were detected.

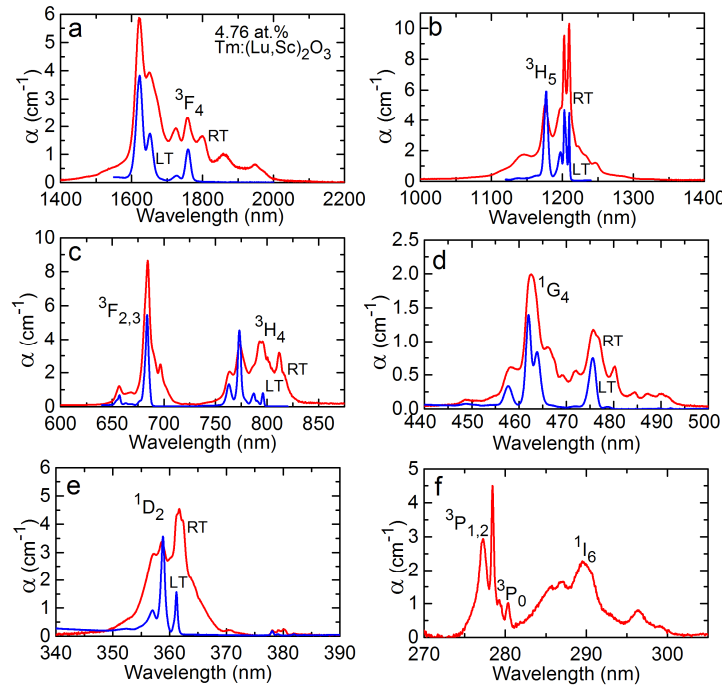


Fig. 3. (a-f) Room-temperature (at 293 K, in red) and low-temperature (at 6 K, in blue, not in scale) absorption spectra of the 4.76 at.%  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  ceramic.

The RT absorption spectrum is shown in Fig. 3. The absorption band at 1.4-2.1  $\mu\text{m}$  is associated with the  ${}^3\text{H}_6 \rightarrow {}^3\text{F}_4$  transition of  $\text{Tm}^{3+}$ . The maximum  $\sigma_{\text{abs}}$  for this transition is  $4.26 \times 10^{-21} \text{ cm}^2$  at 1622 nm. This band is suitable for in-band pumping of  $\text{Tm}^{3+}$  ions, e.g., by Raman-shifted Er fiber lasers [25]. The band at 0.74-0.83  $\mu\text{m}$  corresponds to the  ${}^3\text{H}_6 \rightarrow {}^3\text{H}_4$  transition and it renders the  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  ceramics suitable for pumping with AlGaAs laser diodes. Its maximum  $\sigma_{\text{abs}}$  is  $2.80 \times 10^{-21} \text{ cm}^2$  at 793 nm with a FWHM of  $\sim 25$  nm. At shorter wavelengths, the transitions to the  ${}^3\text{F}_{2,3}$  (0.64-0.71  $\mu\text{m}$ ),  ${}^1\text{G}_4$  (0.45-0.49  $\mu\text{m}$ ),  ${}^1\text{D}_2$  (0.35-0.37  $\mu\text{m}$ ) and  ${}^3\text{P}_{0,2} + {}^1\text{I}_6$  (0.27-0.30  $\mu\text{m}$ ) excited states were also observed. The last one overlaps with the UV absorption edge of the  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  ceramic at  $\lambda_g = 282 \text{ nm}$  ( $E_g = 4.4 \text{ eV}$ ).

The low-temperature absorption spectra of the Tm:(Lu,Sc)<sub>2</sub>O<sub>3</sub> ceramic are also shown in Fig. 3 (in blue, not in scale with respect to the RT spectra). Due to the compositional disorder, the absorption spectra are very broad even at 6 K and the transitions to the individual Stark levels are not completely resolved.

The absorption bands of the Tm<sup>3+</sup> ion in the (Lu,Sc)<sub>2</sub>O<sub>3</sub> ceramic related to the transitions from the <sup>3</sup>H<sub>6</sub> ground-state to the excited states from <sup>3</sup>F<sub>4</sub> to <sup>1</sup>D<sub>2</sub> were analyzed using the standard Judd-Ofeldt (J-O) theory [26,27]. The absorption oscillator strengths were determined from the measured absorption spectra:

$$f_{\Sigma}^{\text{exp}}(JJ') = \frac{m_e c^2}{\pi e^2 N_{\text{Tm}} \langle \lambda \rangle^2} \Gamma(JJ'), \quad (1)$$

where  $m_e$  and  $e$  are the electron mass and charge, respectively,  $c$  is the speed of light,  $\Gamma(JJ')$  is the integrated absorption coefficient within the absorption band and  $\langle \lambda \rangle$  is the “center of gravity” of the absorption band. The results are summarized in Table 1.

The values of  $f_{\Sigma}^{\text{exp}}$  were used to determine the J-O (intensity) parameters,  $\Omega_k$ ,  $k = 2, 4, 6$ :  $\Omega_2 = 2.429$ ,  $\Omega_4 = 1.078$  and  $\Omega_6 = 0.653$  [ $10^{-20}$  cm<sup>2</sup>]. Using these parameters, the absorption oscillator strengths were calculated showing a good agreement with the experiment (as indicated by a moderate root-mean-square (rms) deviation, 0.35):

$$f_{\Sigma}^{\text{calc}}(JJ') = \frac{8}{3h(2J'+1)\langle \lambda \rangle} \frac{(n^2+2)^2}{9n} S_{\text{ED}}^{\text{calc}}(JJ') + f_{\text{MD}}^{\text{calc}}(JJ'), \quad (2a)$$

$$S_{\text{ED}}^{\text{calc}}(JJ') = \sum_{k=2,4,6} U^{(k)} \Omega_k, \quad \text{where } U^{(k)} = \langle (4f^n)SLJ || U^{(k)} || (4f^n)S'L'J' \rangle^2. \quad (2b)$$

Here,  $S_{\text{ED}}^{\text{calc}}$  are the line strengths,  $h$  is the Planck constant,  $n$  is the refractive index of the crystal and  $U^{(k)}$  are the squared reduced matrix elements [28]. The J-O theory describes the electric-dipole (ED) transitions. The contribution of the magnetic-dipole (MD) transition with  $J-J' = 0, \pm 1$  (for the <sup>3</sup>H<sub>6</sub>→<sup>3</sup>H<sub>5</sub> transition),  $f_{\text{MD}}^{\text{calc}}$ , was taken from [29].

**Table 1. Experimental and Calculated Absorption Oscillator Strengths for 4.76 at.% Tm:(Lu,Sc)<sub>2</sub>O<sub>3</sub> Ceramic**

Transition	$\langle \lambda \rangle$ , nm	$\langle E \rangle$ , cm <sup>-1</sup>	$\Gamma$ , cm <sup>-1</sup> nm	$f_{\Sigma}^{\text{exp}} \times 10^6$	$f_{\Sigma}^{\text{calc}} \times 10^6$
<sup>3</sup> H <sub>6</sub> → <sup>3</sup> F <sub>4</sub>	1709	5851	716.3	2.007	2.053 <sup>ED</sup>
<sup>3</sup> H <sub>6</sub> → <sup>3</sup> H <sub>5</sub>	1190	8401	381.1	2.202	1.223 <sup>ED</sup> + 0.525 <sup>MD</sup>
<sup>3</sup> H <sub>6</sub> → <sup>3</sup> H <sub>4</sub>	797.52	12539	160.2	2.061	2.150 <sup>ED</sup>
<sup>3</sup> H <sub>6</sub> → <sup>3</sup> F <sub>2</sub> + <sup>3</sup> F <sub>3</sub>	684.70	14605	118.7	2.072	2.465 <sup>ED</sup>
<sup>3</sup> H <sub>6</sub> → <sup>1</sup> G <sub>4</sub>	467.25	21402	19.9	0.746	0.723 <sup>ED</sup>
<sup>3</sup> H <sub>6</sub> → <sup>1</sup> D <sub>2</sub>	360.05	27774	33.4	2.110	1.897 <sup>ED</sup>
rms deviation					0.35

$\langle \lambda \rangle$  – “center of gravity” of the absorption band,  $\langle E \rangle$  – Energy barycenter of the multiplet,  $\Gamma$  – integrated absorption coefficient,  $f_{\Sigma}^{\text{exp}}$  and  $f_{\Sigma}^{\text{calc}}$  – experimental and calculated absorption oscillator strengths (ED + MD), respectively.

### 3.2 Optical emission

The probabilities for spontaneous radiative transitions were calculated from the corresponding line strengths which were determined from the J-O parameters  $\Omega_k$  and the squared reduced matrix elements  $U^{(k)}$ , see Eq. (2b) [28]:

$$A_{\Sigma}^{\text{calc}}(JJ') = \frac{64\pi^4 e^2}{3h(2J'+1)\langle \lambda \rangle^3} n \left( \frac{n^2+2}{3} \right)^2 S_{\text{ED}}^{\text{calc}}(JJ') + A_{\text{MD}}^{\text{calc}}(JJ'). \quad (3)$$

The MD contributions  $A_{\text{MD}}^{\text{calc}}$  were taken from [29]. Using the values of  $A_{\Sigma}^{\text{calc}}$  for the separate emission channels  $J \rightarrow J'$ , the total probability,  $A_{\text{tot}}$ , the corresponding radiative lifetime of the

excited state,  $\tau_{\text{rad}}$ , and the luminescence branching ratios for the emission channels,  $B(JJ')$  were determined:

$$\tau_{\text{rad}} = \frac{1}{A_{\text{tot}}} \text{ and } B(JJ') = \frac{A_{\Sigma}^{\text{calc}}(JJ')}{A_{\text{tot}}}, \text{ where } A_{\text{tot}} = \sum_{J'} A_{\Sigma}^{\text{calc}}(JJ'). \quad (4)$$

The results are shown in Table 2. The calculated radiative lifetime of the lowest excited state is  $\tau_{\text{rad}}(^3F_4) = 4.01$  ms. Previously, luminescence decay studies of a 1 at.% Tm:LuScO<sub>3</sub> single crystal [30] and a 2 at.% Tm:LuScO<sub>3</sub> ceramic [22] revealed a lifetime  $\tau_{\text{lum}}(^3F_4)$  of 3.84 and 3.2 ms, respectively. The J-O modelling also predicts the radiative lifetime of the  $^3H_4$  pump level,  $\tau_{\text{rad}}(^3H_4) = 0.72$  ms. In [30] for a 1 at.% Tm:LuScO<sub>3</sub> crystal,  $\tau_{\text{lum}}(^3H_4)$  was measured to be 55  $\mu\text{s}$  while no values for the LuScO<sub>3</sub> crystals with lower doping are available (e.g., for 0.2 at.% Tm:Lu<sub>2</sub>O<sub>3</sub> crystal,  $\tau_{\text{lum}}(^3H_4) = 300$   $\mu\text{s}$ ).

The stimulated emission (SE) cross-sections,  $\sigma_{\text{SE}}$ , for the  $^3F_4 \rightarrow ^3H_6$  transition of Tm<sup>3+</sup> in (Lu,Sc)<sub>2</sub>O<sub>3</sub> ceramic were calculated from the measured absorption spectrum, see Fig. 3(a), using the modified reciprocity method [31]:

$$\sigma_{\text{SE}}(\lambda) = \frac{1}{8\pi n^2 \tau_{\text{rad}} c} \frac{\sigma_{\text{abs}}(\lambda) e^{-hc/(kT\lambda)}}{\int \lambda^{-4} \sigma_{\text{abs}}(\lambda) e^{-hc/(kT\lambda)} d\lambda}. \quad (5)$$

Here,  $k$  is the Boltzmann constant,  $T$  is the crystal temperature (RT),  $\tau_{\text{rad}}$  is the radiative lifetime of the emitting state ( $^3F_4$ ). To reduce the error in  $\sigma_{\text{SE}}$  at long wavelengths ( $> 2$   $\mu\text{m}$ ) originating from the exponential term in Eq. (5), we additionally used the Füchtbauer–Ladenburg (F-L) equation [32] which is adequate because of the negligible reabsorption in this spectral range, Fig. 3(a). The  $\sigma_{\text{SE}}$  spectrum is shown in Fig. 4(a). The maximum  $\sigma_{\text{SE}}$  amounts to  $7.15 \times 10^{-21}$  cm<sup>2</sup> at 1951 nm. Above 2  $\mu\text{m}$  where laser operation is expected for low-loss cavities, a local maximum of  $\sigma_{\text{SE}} = 2.38 \times 10^{-21}$  cm<sup>2</sup> is found at 2090 nm.

**Table 2. Calculated Emission Probabilities for Tm<sup>3+</sup> in (Lu,Sc)<sub>2</sub>O<sub>3</sub> Ceramic**

Excited state	Terminal state	$\langle \lambda \rangle$ , nm	$A_{\Sigma}^{\text{calc}}(JJ')$ , s <sup>-1</sup>	$B(JJ')$ , %	$A_{\text{tot}}$ , s <sup>-1</sup>	$\tau_{\text{rad}}$ , ms
$^3F_4$	$^3H_6$	1709	249.15 <sup>ED</sup>	100	249.15	4.01
$^3H_5$	$^3F_4$	3921	7.25 <sup>ED</sup> + 1.39 <sup>MD</sup>	2.4	363.35	2.75
	$^3H_6$	1190	252.51 <sup>ED</sup> + 102.19 <sup>MD</sup>	97.6		
$^3H_4$	$^3H_5$	2417	21.74 <sup>ED</sup> + 12.78 <sup>MD</sup>	2.5	1383.5	0.72
	$^3F_4$	1495	98.19 <sup>ED</sup> + 28.49 <sup>MD</sup>	9.2		
	$^3H_6$	797.5	1222.3 <sup>ED</sup>	88.3		
$^3F_2 + ^3F_3$	$^3H_4$	4840	5.66 <sup>ED</sup> + 0.31 <sup>MD</sup>	0.2	2549.2	0.39
	$^3H_5$	1612	344.62 <sup>ED</sup>	13.5		
	$^3F_4$	1142	67.08 <sup>ED</sup> + 73.34 <sup>MD</sup>	5.5		
	$^3H_6$	684.7	2058.2 <sup>ED</sup>	80.8		
$^1G_4$	$^3F_2$	1619	15.72 <sup>ED</sup>	0.6	2647.8	0.38
	$^3F_3$	1471	52.08 <sup>ED</sup> + 4.22 <sup>MD</sup>	2.1		
	$^3H_4$	1128	244.76 <sup>ED</sup> + 41.22 <sup>MD</sup>	10.8		
	$^3H_5$	769.2	671.99 <sup>ED</sup> + 188.91 <sup>MD</sup>	32.5		
	$^3F_4$	643.0	168.92 <sup>ED</sup> + 11.48 <sup>MD</sup>	6.8		
	$^3H_6$	467.3	1248.5 <sup>ED</sup>	47.2		

$\langle \lambda \rangle$  - calculated mean wavelength of the emission band,  $A_{\Sigma}^{\text{calc}}$  - probability of the radiative spontaneous transition (ED + MD),  $B(JJ')$  - luminescence branching ratio,  $A_{\text{tot}}$  and  $\tau_{\text{rad}}$  - total probability of radiative spontaneous transitions and radiative lifetime of the excited state, respectively

The gain cross-section,  $\sigma_g = \beta\sigma_{\text{SE}} - (1 - \beta)\sigma_{\text{abs}}$ , where  $\beta = N(^3F_4)/N_{\text{Tm}}$  is the inversion ratio, is typically calculated to estimate the expected laser wavelength, see Fig. 4(b). For low  $\beta < 0.06$ , broad and smooth gain spectra are observed centered at  $\sim 2.10$   $\mu\text{m}$ . For higher  $\beta$ , a peak at 1.97  $\mu\text{m}$  and further one at 1.95  $\mu\text{m}$  dominate the spectrum.

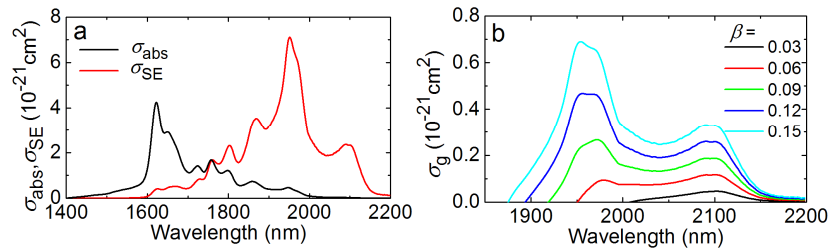


Fig. 4. Spectroscopy of  $\text{Tm}^{3+}$ -doped  $(\text{Lu,Sc})_2\text{O}_3$  ceramic: (a) absorption,  $\sigma_{abs}$ , and stimulated-emission,  $\sigma_{SE}$ , cross-sections for the  ${}^3\text{H}_6 \leftrightarrow {}^3\text{F}_4$  transition; (b) gain cross-sections,  $\sigma_g = \beta\sigma_{SE} - (1 - \beta)\sigma_{abs}$ , for the  ${}^3\text{F}_4 \rightarrow {}^3\text{H}_6$  transition.  $\beta = N({}^3\text{F}_4)/N_{\text{Tm}}$  is the inversion ratio.

## 4. Continuous-wave laser operation

### 4.1 Laser set-up

The laser experiments were performed in a compact microchip-type cavity, Fig. 5(a). The 2.91 mm-thick polished and uncoated  $\text{Tm}:(\text{Lu,Sc})_2\text{O}_3$  ceramic active element (AE) with an aperture of  $3.01 \times 3.06 \text{ mm}^2$  was mounted in a water cooled ( $12^\circ\text{C}$ ) Cu-holder. Indium foil was used to provide a better thermal contact from all 4 lateral sides of the AE. The plano-plano cavity consisted of a flat pump mirror (PM) antireflection (AR) coated for 0.77-1.05  $\mu\text{m}$  and high reflection (HR) coated for 1.80-2.12  $\mu\text{m}$ , and a flat output coupler (OC) with transmission of  $T_{OC} = 1.5\%$ , 3% or 5% at 1.84-2.12  $\mu\text{m}$ . Both PM and OC were placed close to the AE with minimum air gaps, so that the geometrical cavity length was  $\sim 3 \text{ mm}$ . The AE was pumped through the PM by a fiber-coupled AlGaAs laser diode (LuOcean model Lu0808D200, Lumics, fiber core diameter: 200  $\mu\text{m}$ , NA: 0.22) emitting randomly polarized output at 802 nm (the wavelength was stabilized by water-cooling of the diode). We used a lens assembly (focal length: 30 mm, 1:1 imaging ratio) to focus the pump light into the AE. The radius of the pump beam in the crystal was 100  $\mu\text{m}$  (confocal parameter of the pump beam  $2z_R = 1.9 \text{ mm}$ ). The OCs provided a partial reflection ( $R \approx 40\%$ ) at the pump wavelength. The total pump absorption under lasing conditions was 48%.

The laser emission spectra were measured with a compact spectrometer (WaveScan, sensitivity: 1.0-2.6  $\mu\text{m}$ , APE GmbH). The beam profile was captured in the far-field using a FIND-R-SCOPE near-IR camera (model 85726, sensitivity: 0.4-2.2  $\mu\text{m}$ ), see Fig. 5(b).

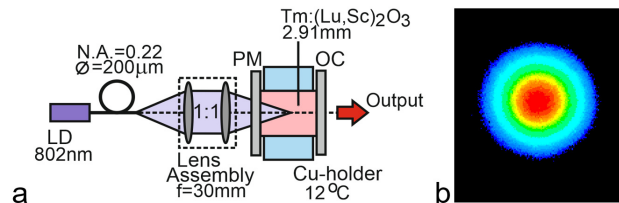


Fig. 5.  $\text{Tm}:(\text{Lu,Sc})_2\text{O}_3$  ceramic microchip laser: (a) scheme of the laser, LD – laser diode, PM – pump mirror, OC – output coupler; (b) laser beam profile captured at  $P_{abs} = 5.05 \text{ W}$ , corresponding to an output power of 1.01 W for  $T_{OC} = 3\%$ .

### 4.2 Microchip laser operation

Microchip laser operation has been achieved with all OCs. This indicates a positive thermal lens (and positive  $dn/dT$  coefficient) for  $\text{Tm}:(\text{Lu,Sc})_2\text{O}_3$  ceramics. The laser output was randomly polarized. The input-output dependences are shown in Fig. 6(a). The maximum output power reached 1.01 W at 2095-2102 nm with a slope efficiency  $\eta = 24\%$  (with respect to the absorbed pump power,  $P_{abs}$ ) for  $T_{OC} = 3\%$ . The laser threshold was at  $P_{abs} = 0.86 \text{ W}$  and the optical-to-optical efficiency  $\eta_{opt}$  was 10% (with respect to the incident power). For  $T_{OC} = 1.5\%$ , slightly lower  $\eta = 19\%$  was observed. For both OCs, the output dependence was linear

up to  $P_{\text{abs}} \sim 5$  W where thermal fracture was observed. For  $T_{\text{OC}} = 5\%$ , the laser output deteriorated (96 mW with  $\eta = 8\%$ ) which is attributed to stronger upconversion losses and the associated heating. Typical laser emission spectra are presented in Fig. 6(b). The laser emission occurred at  $\sim 2.09 \mu\text{m}$  in agreement with the gain spectra of  $\text{Tm}^{3+}$  for low inversion ratios  $\beta < 0.06$ , Fig. 4(b). A small  $\beta$  is expected for the utilized low output coupling. The multi-peak spectral behavior is due to etalon effects.

The  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  ceramic microchip laser generated a nearly-circular output beam with a measured  $M_{x,y}^2 < 1.2$  (at  $P_{\text{abs}} = 5.05$  W, for  $T_{\text{OC}} = 3\%$ ), see Fig. 5(b).

As compared with a previous report on a 2 at.%  $\text{Tm}:\text{LuScO}_3$  ceramic emitting at 1982 nm [22], the laser characteristics in the present work are considerably improved. In [22], under diode-pumping at 790 nm, the maximum output power was limited to 211 mW (at  $P_{\text{abs}} \sim 3.5$  W) by thermal roll-over with a slope efficiency of only 8%. Here, despite the higher Tm doping, the ceramic quality allowed to work at higher pump levels to achieve an output power as high as  $\sim 1$  W at 3 times higher slope efficiency.

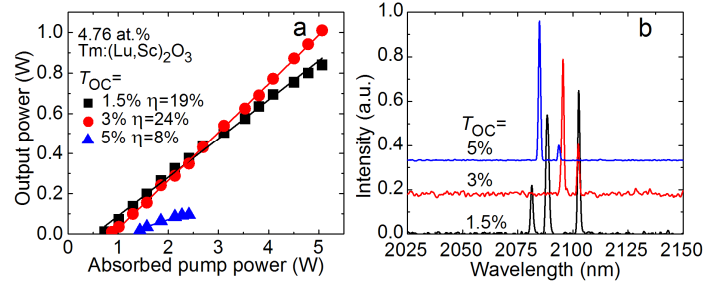


Fig. 6.  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  ceramic microchip laser: (a) input-output dependences,  $\eta$  – slope efficiency; (b) typical laser emission spectra measured at  $P_{\text{abs}} = 5.05$  W (for  $T_{\text{OC}} = 1.5\%$  and 3%) and 2.40 W ( $T_{\text{OC}} = 5\%$ ).

## 5. Comparison of ceramics with a single crystal

For the comparative spectroscopic and laser studies, we used a 1.0 at.%  $\text{Tm}:\text{LuScO}_3$  crystal grown by the heat-exchanger method (HEM) [30].

At first, we compare the spectroscopic properties of the single crystal and the ceramic. The absorption cross-section spectra for the  $^3\text{H}_6 \rightarrow ^3\text{H}_4$  transition are shown in Fig. 7(a). The spectra are similar in shape while less structured for the ceramics. The maximum  $\sigma_{\text{abs}}$  of  $2.60 \times 10^{-21} \text{ cm}^2$  for the  $\text{Tm}:\text{LuScO}_3$  single crystal is observed at 793 nm. It is known that for the  $\text{Tm}^{3+}$  ion in a “mixed”  $\text{LuScO}_3$  crystal,  $\sigma_{\text{abs}}$  is lower compared to  $\text{Tm}:\text{Lu}_2\text{O}_3$  and  $\text{Tm}:\text{Sc}_2\text{O}_3$  [30] due to a compositional disorder. A similar effect is expected for “mixed” ceramics.

The SE cross-section spectra for the  $^3\text{F}_4 \rightarrow ^3\text{H}_6$  transition for the single crystal and the ceramic are compared in Fig. 7(b). A slight reduction of  $\sigma_{\text{SE}}$  for the ceramic is observed: for the  $\text{Tm}:\text{LuScO}_3$  single crystal, the maximum  $\sigma_{\text{SE}}$  is  $8.0 \times 10^{-21} \text{ cm}^2$  at 1956 nm. The  $\sigma_{\text{SE}}$  value for the single crystal determined with the F-L method can be overestimated as compared to that obtained by the reciprocity method in analogy to  $\text{Tm}:\text{Lu}_2\text{O}_3$  [30]. The physical reason is the shorter measured luminescence decay time  $\tau_{\text{lum}}$  for  $\text{Tm}:\text{A}_2\text{O}_3$  crystals than the radiative one  $\tau_{\text{rad}}$ . The peak in the SE cross-section spectra at  $>2 \mu\text{m}$  is shifted to a longer wavelength for the  $\text{Tm}:\text{LuScO}_3$  single-crystal (2098 nm) due to the larger fraction of  $\text{Sc}^{3+}$  ions as compared to the ceramic.

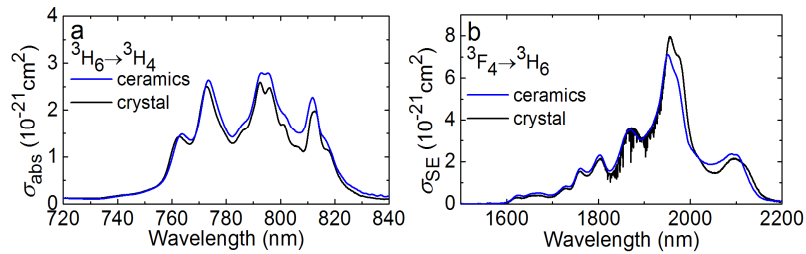


Fig. 7. Spectroscopy of  $\text{Tm}^{3+}$  in a 4.76 at.%  $\text{Tm}:(\text{Lu}_{2/3}\text{Sc}_{1/3})_2\text{O}_3$  ceramic and in a 1 at.%  $\text{Tm}:\text{LuScO}_3$  single-crystal: (a)  $\sigma_{\text{abs}}$  spectra for the  ${}^3\text{H}_6 \rightarrow {}^3\text{H}_4$  transition, (b)  $\sigma_{\text{SE}}$  spectra for the  ${}^3\text{F}_4 \rightarrow {}^3\text{H}_6$  transition. The noise of the black curve in (b) is due to water absorption affecting the measured luminescence spectrum.

For the laser experiments with the  $\text{Tm}:\text{LuScO}_3$  single-crystal, we cut a 2.91 mm-thick cubic active element with an aperture of  $2.82 \times 3.13 \text{ mm}^2$ . It was polished to laser-grade quality and remained uncoated. The experiments were performed in the set-up depicted in Fig. 5(a). Microchip laser operation has been achieved and the results are presented in Fig. 8. Due to the observed degradation of the  $\text{Tm}:\text{LuScO}_3$  laser output for  $T_{\text{OC}} > 3\%$ , we additionally studied a high-reflective OC ( $T_{\text{OC}} = 0.2\%$ ). The laser emission was randomly polarized. The output power reached 221 mW at 2092-2095 nm with  $\eta = 21\%$  for  $T_{\text{OC}} = 1.5\%$ . The laser threshold was at  $P_{\text{abs}} = 0.38 \text{ W}$  and  $\eta_{\text{opt}}$  was 7%.

Previously, a similar crystal with a thickness of 3 mm was studied under Ti:Sapphire pumping at 796 nm [15,30]. The output power was 324 mW at 1978-1992 nm with  $\eta = 40\%$  (for  $T_{\text{OC}} = 1.5\%$ ). This is comparable to our result considering the better quality of the pump beam from the Ti:Sapphire laser. Using a 7.7 mm-thick sample, the same authors extracted 705 mW at 2090-2115 nm with  $\eta = 55\%$  (at a maximum  $P_{\text{abs}} = 1.4 \text{ W}$ ) [30].

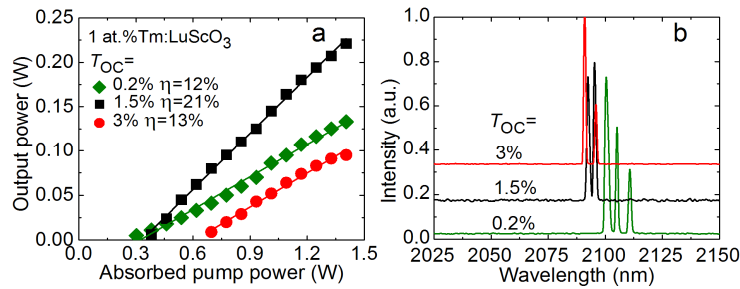


Fig. 8.  $\text{Tm}:\text{LuScO}_3$  single crystal microchip laser: (a) input-output dependences,  $\eta$  – slope efficiency; (b) typical laser emission spectra measured at  $P_{\text{abs}} = 1.41 \text{ W}$ .

## 6. Conclusion

“Mixed” sesquioxide  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  transparent ceramics produced by the HIP method are promising materials for broadly tunable CW and ultrashort (femtosecond) ML oscillators at 1.95-2.1  $\mu\text{m}$ . They allow for high  $\text{Tm}^{3+}$  doping levels by keeping the optical quality high, size-scalable synthesis, and similar spectroscopic properties as compared to those for HEM-grown  $\text{Tm}:\text{LuScO}_3$  single crystals. In the present work, we report on the first transparent ceramics with composition  $(\text{Lu}_{2/3}\text{Sc}_{1/3})_2\text{O}_3$  doped with 4.76 at.% Tm. Their morphology, structure and vibronic properties are studied. The transition probabilities of  $\text{Tm}^{3+}$  ions are determined within the J-O theory. The ceramic provides broad and smooth gain spectra at 1.9-2.15  $\mu\text{m}$ , as well as relatively high stimulated-emission cross-section at  $>2 \mu\text{m}$ , namely  $2.38 \times 10^{-21} \text{ cm}^2$  at 2090 nm. Using the  $\text{Tm}:(\text{Lu},\text{Sc})_2\text{O}_3$  ceramic in a compact diode-end-pumped microchip laser, watt-level output at  $\sim 2.1 \mu\text{m}$  has been achieved with a slope efficiency of 24%, representing the highest output power demonstrated for any  $\text{Tm}^{3+}$ -doped  $(\text{Lu},\text{Sc})_2\text{O}_3$  crystalline or ceramic laser material.

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